SILICON (Si) POWER MOSFET A CEP18N5A



CET MOS

CEP18N5A

500V ▲ 0.24Ω ▲ 18A ▲ Si MOSFET

SILICON Si MOSFET ▲ THT type N-channel enhancement mode UL94V-0 rated flame retardant epoxy TO220-3L package Super high dense cell density for extremely low R_{DS(ON)} High power and current handling capability







MAXIMUM RATINGS

Parameter (T _c = 25°C, unless otherwise noted)		Characteristics
Drain-Source Voltage	V _{DS}	500V
Gate-Source Voltage	V _{GS}	±30V
Continuous Drain Current at T _c = 25°C	Ι _D	18A
Continuous Drain Current at T _c = 100°C	Ι _D	11A
Pulsed Drain Current Note 1	IDM Note 5	72A
Maximum Power Dissipation at T _c = 25°C	PD	208W
Power Dissipation Derating above 25°C	ΔP _D	1.6W/°C
Single Pulsed Avalanche Energy Note 6	E _{AS}	859mJ
Single Pulsed Avalanche Current Note 6	I _{AS}	18A
Operating and Storage Temperature Range	T _J , T _{STG}	-55°C to +150°C

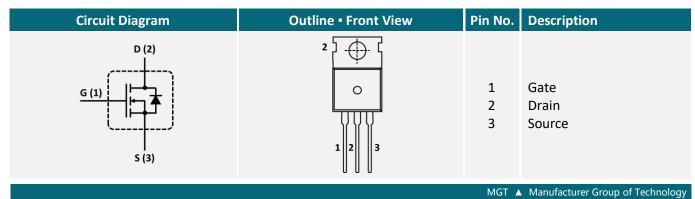
THERMAL CHARACTERISTICS

Parameter	Symbol	Limit
Thermal Resistance, Junction-to-Case	R _{TH_JC}	0.6°C/W
Thermal Resistance, Junction-to-Ambient	R _{th_ja}	62.5°C/W

APPLICATIONS

General Lighting	Industrial	Motors	Power	UPS
LED & CCFL	Inverters	& Drives	Supplies	
-Ò,-	0			

PIN DESCRIPTION



CEP18N5A ▲ Rev.001 ▲ Date: 30/09/2022 ▲ Page: 1

Copyright by MGT A www.mgt.co.com All rights reserved The information in this document is subject to change without notice.



CET MOS

ELECTRICAL CHARACTERISTICS A T_c = 25°C, unless otherwise noted

ltem	Condition	Symbol	Min.	Тур.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV _{DSS}	500			V
Zero Gate Voltage Drain Current	V_{DS} = 500V, V_{GS} = 0V	I _{DSS}			1	μA
Gate Body Leakage Current, Forward	$V_{GS} = 30V, V_{DS} = 0V$	I _{GSSF}			100	nA
Gate Body Leakage Current, Reverse	V_{GS} = -30V, V_{DS} = 0V	I _{GSSR}			-100	nA
On Characteristics Note 2						
Gate Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250 \mu A$	V _{GS(th)}	2		4	V
Static Drain-Source On-Resistance	$V_{GS} = 10V$, $I_D = 9A$	R _{DS(ON)}		0.24	0.27	Ω
Dynamic Characteristics Note 3						
Input Capacitance	V_{DS} = 25V, V_{GS} = 0V, f = 1MHz	CISS		2465		рF
Output Capacitance	V_{DS} = 25V, V_{GS} = 0V, f = 1MHz	Coss		300		рF
Reverse Transfer Capacitance	V_{DS} = 25V, V_{GS} = 0V, f = 1MHz	C _{RSS}		10		pF
Switching Characteristics Note 3						
Turn-On Delay Time	V_{DD} = 250V, V_{GS} = 10V, I_{D} = 18A, $R_{\text{G}(\text{ext})}$ = 25 Ω	t _{D(ON)}		36		ns
Turn-On Rise Time	V_{DD} = 250V, V_{GS} = 10V, I_{D} = 18A, $R_{\text{G}(\text{ext})}$ = 25 Ω	t _R		28		ns
Turn-Off Delay Time	V_{DD} = 250V, V_{GS} = 10V, I_{D} = 18A, $R_{\text{G}(\text{ext})}$ = 25 Ω	t _{D(OFF)}		78		ns
Turn-Off Fall Time	V_{DD} = 250V, V_{GS} = 10V, I_{D} = 18A, $R_{G(\text{ext})}$ = 25 Ω	t _F		11		ns
Total Gate Charge	V_{DS} = 400V, V_{GS} = 10V, I_{D} = 18A	Q_{G}		58		nC
Gate Source Charge	V_{DS} = 400V, V_{GS} = 10V, I_{D} = 18A	Q _{GS}		11		nC
Gate Drain Charge	V_{DS} = 400V, V_{GS} = 10V, I_D = 18A	\mathbf{Q}_{GD}		23		nC
Drain-Source Diode Characteristics a	nd Maximum Ratings					
Drain-Source Diode Forward Current		ls			18	А
Drain-Source Diode Forward Voltage Note 2	V _{GS} = 0V, I _S = 18A	V_{SD}			1.4	V

Notes

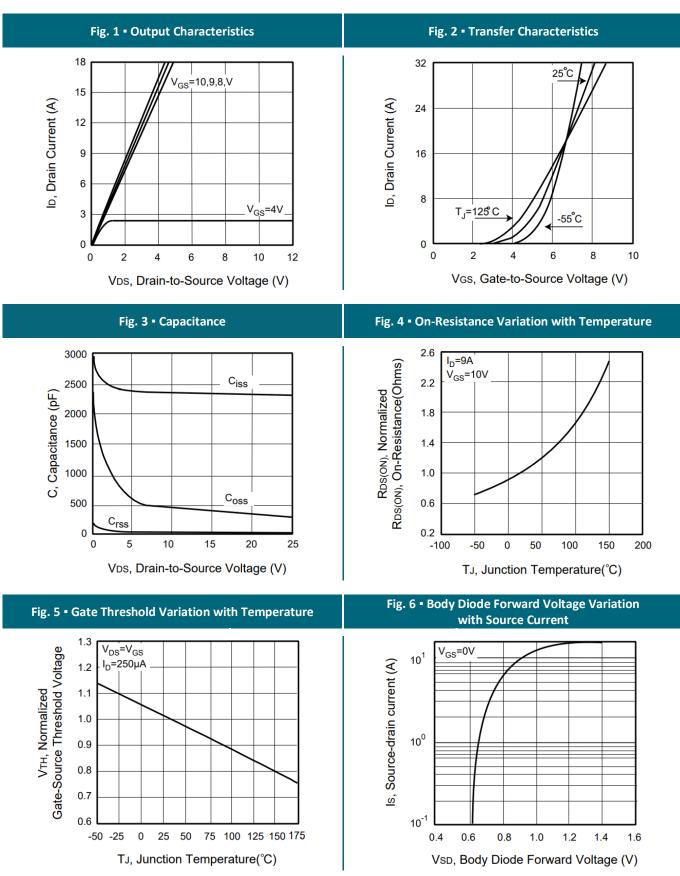
- 1: Repetitive Rating: Pulse width limited by maximum junction temperature
- 2: Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.
- 3: Guaranteed by design, not subject to production testing.
- 4: Limited only by maximum temperature allowed.
- 5: Pulse width limited by safe operating area.
- 6: L = 5.3mH, I_{AS} = 18A, V_{DD} = 50V, R_G = 25 Ω , Starting T_J = 25°C



MGT **A** Manufacturer Group of Technology

CET MOS

REFERENCE DATA ▲ TYPICAL DEVICE PERFORMANCE



CEP18N5A ▲ Rev.001 ▲ Date: 30/09/2022 ▲ Page: 3

Copyright by MGT **A** www.mgt.co.com **A** All rights reserved **A** The information in this document is subject to change without notice.



CET MOS

REFERENCE DATA A TYPICAL DEVICE PERFORMANCE

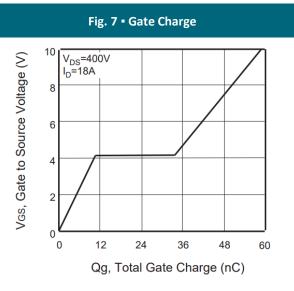
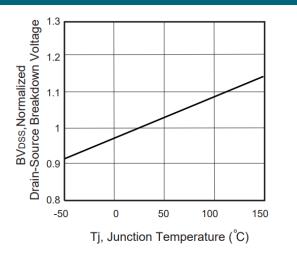
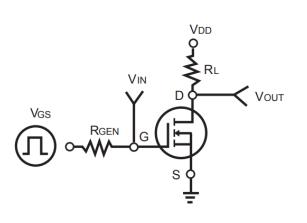


Fig. 9 - Breakdown Voltage Variation vs. Temperature







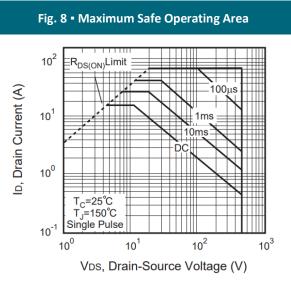
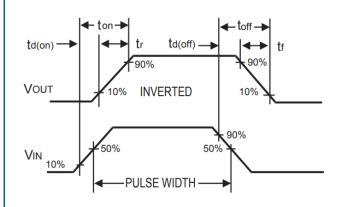


Fig. 11 - Switching Waveforms



MGT 🔺 Manufacturer Group of Technology

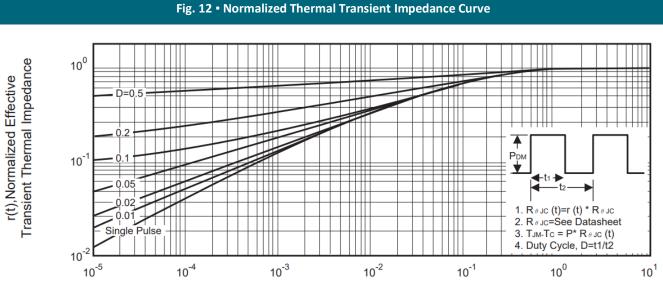
CEP18N5A ▲ Rev.001 ▲ Date: 30/09/2022 ▲ Page: 4

Copyright by MGT **A** www.mgt.co.com **A** All rights reserved **A** The information in this document is subject to change without notice.



CET MOS

REFERENCE DATA A TYPICAL DEVICE PERFORMANCE



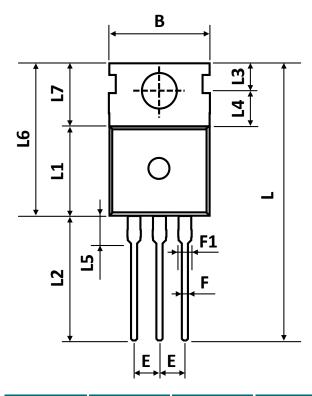
Square Wave Pulse Duration (msec)

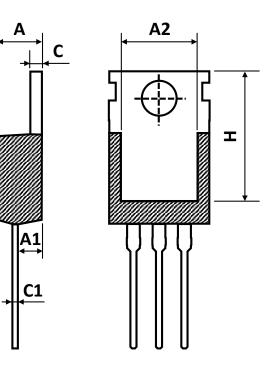
MGT **A** Manufacturer Group of Technology



SILICON (Si) POWER MOSFET A CEP18N5A

PACKAGE OUTLINE





Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
А	4.43	4.53	4.63
A1	2.30	2.40	2.50
A2	7.70	7.90	8.10
В	9.80	10.00	10.20
С	1.25	1.30	1.40
C1	0.45	0.50	0.60
D	3.45	3.60	3.70
E	2.45	2.54	2.60
F	0.70	0.80	0.95
F1	1.15	1.33	1.50
L	26.80	28.80	30.80
L1	9.20	9.30	9.40
L2	12.80	13.10	13.40
L3	2.70	2.80	2.90
L4	3.50	3.70	3.80
L5	2.60	2.90	3.20
L6	15.40	15.80	16.20
L7	6.20	6.50	6.80
Н	12.95	13.25	13.55

ORDERING INFORMATION

Part Number	Package	Packing	Tube Qty.	Inner Box Qty.	Outer Box Qty.
CEP18N5A	TO-220-3L	Tube	50pcs	1,000pcs	4,000pcs
				MGT 🔺 Manufactu	rer Group of Technology

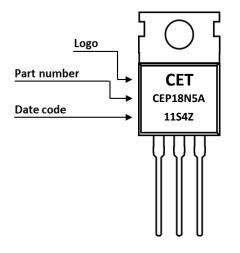
Copyright by MGT **A** www.mgt.co.com **A** All rights reserved **A** The information in this document is subject to change without notice.

SILICON (Si) POWER MOSFET A CEP18N5A



CET MOS

PART MARKING



DATE CODE

Example: 11S4Z



| Product Type Z: Pb-free G: Green Product

	Coding list for "Day"								
1	2	3	4	5	6	7	8	9	A
01	02	03	04	05	06	07	08	09	10
B	C	D	E	F	G	H	 	J	K
11	12	13	14	15	16	17	18	19	20
L	M	N	0	P	Q	R	S	T	U
21	22	23	24	25	26	27	28	29	30
V 31									

Coding list for "Month"

1 Jan	2 Feb		5 May	
7 Jul	8 Aug		B Nov	C Dec

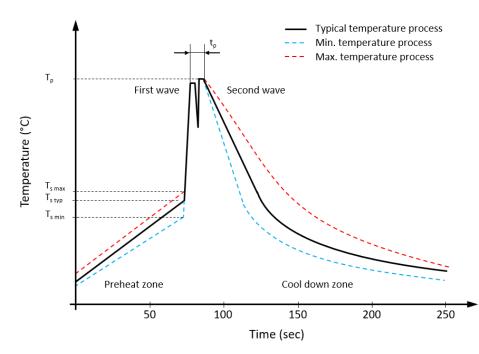
Coding list for "Year"







RECOMMENDED WAVE SOLDERING PROFILE A THT PACKAGE



Classification wave soldering profile ▲ Refer to EN 61760-1: 2006

Profile Features		Value 🛦 Sn-Pb Assembly	Value 🛦 Pb-free Assembly
Preheat temperature min.	$T_{s min}$	100 °C	100 °C
Preheat temperature typical	T _{s typ}	120 °C	120 °C
Preheat temperature max.	$T_{s max}$	130 °C	130 °C
Preheat time t_s from $T_{s min}$ to $T_{s max}$	ts	70 seconds	70 seconds
Peak temperature	Tp	235 °C to 260 °C	245 °C to 260 °C
Time of actual peak temperature	t _p	Max. 10 seconds Max. 5 second each wave	Max. 10 seconds Max. 5 second each wave
Ramp-down date min.		~ 2 °C/second	~ 2 °C/second
Ramp-down rate typical		~ 3.5 °C/second	~ 3.5 °C/second
Ramp-down rate max.		~ 5 °C/second	~ 5 °C/second
Time 25°C to 25°C		4 minutes	4 minutes



REVISION TABLE

Revision	Date	Status	Notes
001	30/09/2022	Initial release	Initial publication

DISCLAIMER

Except for the written expressed warranties, MGT does not implicitly, by assumption or whatever else, warrant, under-take, promise any other warranty or guaranty for any MGT product.

All information and technical specifications made available by MGT are for guidance only and we reserve the right to change or modify them without prior notice. Unless expressly stated in writing by MGT, we reject any guarantees, obligations, or warranties.

All MGT products with the technical specifications described are suitable for use in certain applications. Operating, production, storage and environmental conditions can have a massive influence on the parameters mentioned in the data sheets, which cause the performance to vary over time.

It is subject to the user's duty of care to design and validate his products in such a way that appropriate measures are taken, such as protective circuits or redundant systems to ensure the safety standards required in the application.

MGT components are not designed or rated for use in life support, rescue, safety critical, military, or aerospace applications where failure or malfunction could result in property or environmental damage, serious injury or death. In the aforementioned cases, please contact us before using MGT products.

In principle, we reserve all rights and MGT's general terms and conditions apply. You can find them on our website <u>www.mgt.co.com.</u>